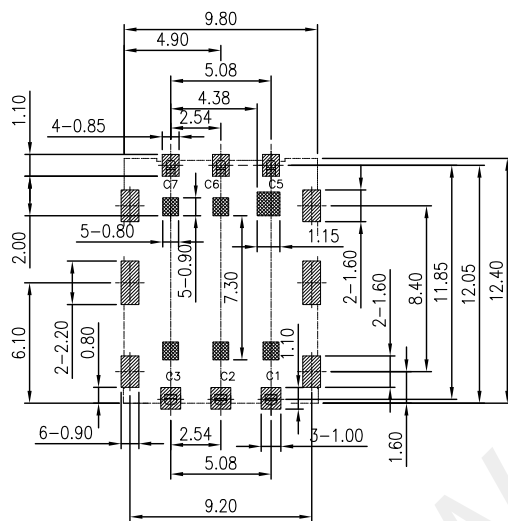
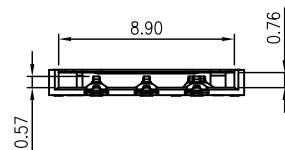
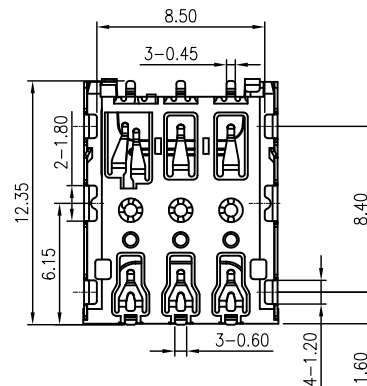
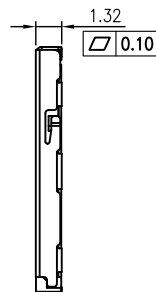
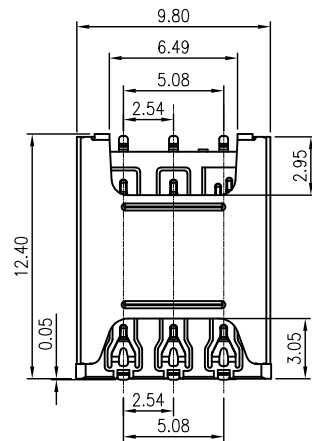
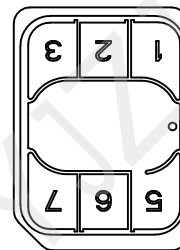


RECOMMENDED P.C.B LAYOUT COMPONENT SIDE (TOLERANCE ± 0.05)

▨ PAD AREA
▨ CONNECTOR DUTLINE
▨ PATTERN
▨ AND A HOLE IN THIS AREA



Nano SIM Circuit Description:

PIN No.	FUNCTION
C1	VCC
C2	RST
C3	CLK
C5	GND
C6	VPP
C7	I/O

TECHNICAL CHARACTERISTICS 1.

1.General Characteristics

Dimensions: 12.40LX9.80WX1.35H mm

Weight: Approx 0.50 $\pm$ 0.2g

Durability: 1,500 cycles min.

2.Electrical Characteristics

Contact resistance: 50m Ω typical,
100m. maxInsulation resistance: >1000M Ω /500V DC

Solderability

Vaporphase: 215 $^{\circ}$ C, 30sec. Max IRreflow: 250 $^{\circ}$ C, 5sec. Max Manual soldering: 370 $^{\circ}$ C, 3sec. Max

4.Environmental Characteristics

Operating temperature: -40 $^{\circ}$ C ~ +85 $^{\circ}$ C

Operating humidity: 10% ~ +95% RH

3	CONTACT	1	COPPER ALLOY	CONTACT AREA: GOLD PLATED
2	SHELL	1	STAINLESS STEEL	
1	HOUSING	1	LCP UL94V-0	COLOR: BLACK
NO.	DESCRIPTION	Q'TY	Material	Finish



深圳市华宇创精密电子有限公司

TOLERANCE: X.X ± 0.30 X.XX ± 0.25 X.XXX ± 0.15 X' $\pm 2^{\circ}$ X.X' $\pm 0.5^{\circ}$	DRAWN BY : 陈一鸣	DATE : 2014-02-23	PART NAME: NANO SIM 6P 1.32H
CHECKED BY: 马跃	DATE : 2014-02-23	PART NO. HYC387-SIM06-132	MOLD NO.
APPROVED BY: 邱敏	DATE : 2014-02-23	DRAW NO: HYC-2602281137	SHEET NO. 1 OF 1